



Product data sheet

1. General description

Hyperfast power diode in a 2-lead IITO220 plastic package.

2. Features and benefits

- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage		600			V	
$I_{F(AV)}$	average forward current	δ = 0.5; T _{mb} ≤ 90 °C; square-wave pulse Fig. 1; Fig. 2; Fig. 3	30			A	
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 90 °C; square-wave pulse	60			A	
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; <u>Fig. 4</u>	200			A	
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		2	20		А
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	- 1.38 1.8		V		
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 7$		-	-	35	ns

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	A	anode		К <u>— Д</u> А 001ааа020
mb	n.c.	mounting base; isolated		001aaa020
			U U	
			1 2 IITO220-2L	

6. Ordering information

Table 3. Ordering information							
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date	
BYC30Y-600P	IITO220-2L	BYC30Y-600PQ	Tube	50	IITO220E-2L	03-Mar-2020	

7. Marking

Table 4. Marking codes	
Type number	Marking codes
BYC30Y-600P	BYC30Y 600P

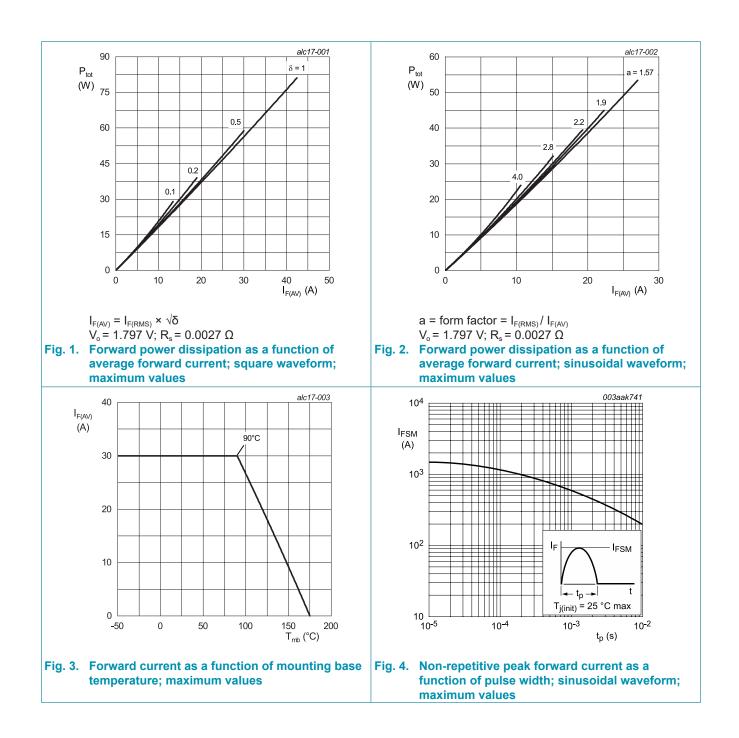
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

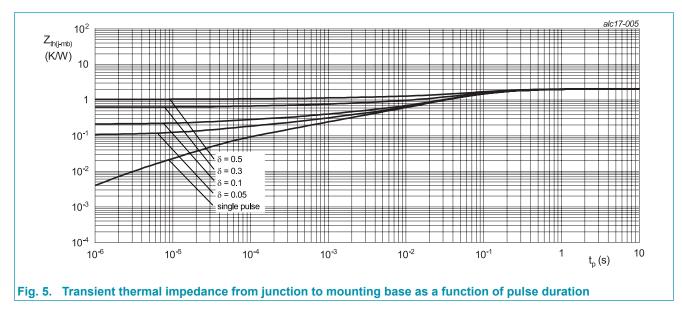
Symbol	Parameter	Conditions	Values	Unit
V _{RRM}	repetitive peak reverse voltage		600	V
V _{RWM}	crest working reverse voltage		600	V
V _R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _{mb} ≤ 90 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	30	A
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 90 °C; square-wave pulse	60	A
I _{FSM}	non-repetitive peak forward current	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4	200	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	А
T _{stg}	storage temperature		-65 to 175	°C
Tj	junction temperature		175	°C

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9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2.1	K/W
$R_{\text{th}(j\text{-}a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

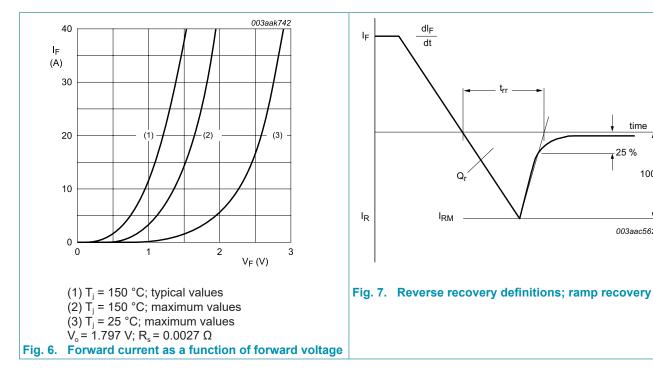


10. Isolation characteristics

Table 7. Iso	olation characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{\text{isol}(\text{RMS})}$	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

11. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 30A; T _j = 25 °C; <u>Fig. 6</u>	-	2	2.75	V
		I _F = 30 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.38	1.8	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	1	mA
Dynamic	characteristics					
Q _r re	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/$ µs; $T_J = 25 \text{ °C}; Fig. 7$	-	50	-	nC
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/$ μ s; $T_J = 125 ^{\circ}\text{C}; \text{ Fig. 7}$	-	280	-	nC
t _{rr} reverse recovery	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$	-	-	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	-	35	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	70	-	ns
I _{RM}	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 ^\circ\text{C}; \text{ Fig. 7}$	-	3.5	-	A
		I _F = 30 A; V _R = 200 V; dI _F /dt = 200 A/μs; T _i = 125 °C; <u>Fig. 7</u>	-	7.6	-	А



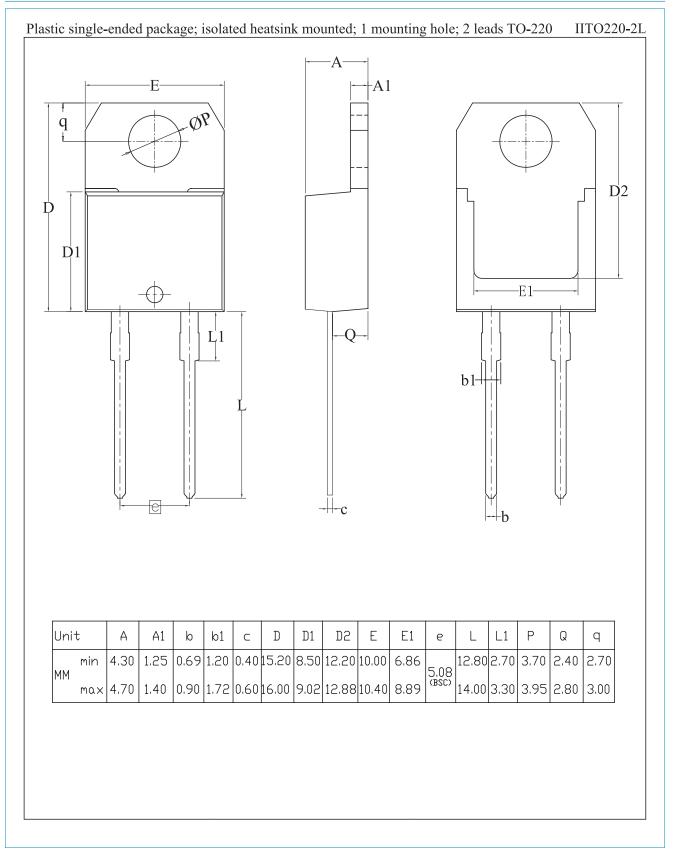
time

003aac562

100 %

25 %

12. Package outline



BYC30Y-600P

Hyperfast power diode

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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